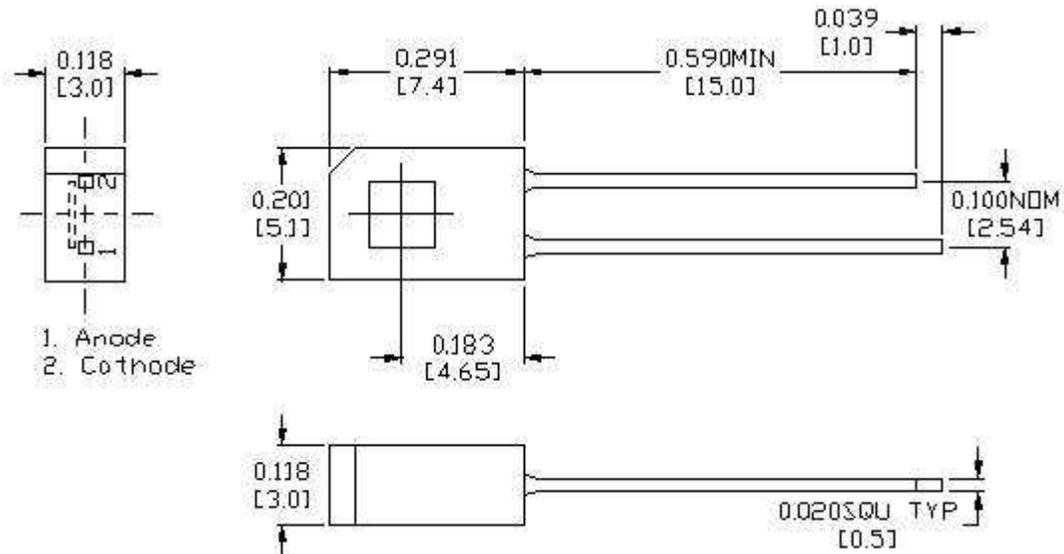


DESCRIPTION

This is a Silicon Photo Diode optimized for applications requiring a wide viewing angle and a side-looking package.

FEATURES

- High Responsivity
- Wide Viewing Angle
- Side-looking Plastic Package



ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -20°C to +85°C
- Case operating temperature..... 0°C to +70°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 35 Volts

OUTLINE DIMENSIONS

Tolerances are +/- 0.005 inches, except as noted
 The case is electrically isolated from the pins

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	$V_r = 10 \text{ V}, f = 1 \text{ MHz}$	C		10		pF
Open Circuit Voltage	$H = 5.0 \text{ mW/cm}^2$	VOC		350		mV
Short Circuit Current	$H = 5.0 \text{ mW/cm}^2$	ISC	50	75		μA
Dark Current	$V_r = 10 \text{ Volts}, H = 0 \text{ mW}$	I_d		5	30	nA
Response Time	10%-90%, $V_r = 10 \text{ Volts}$ $R_L = 1 \text{ K}\Omega$	t_r		50		nsec
		t_f		50		nsec
Peak Wavelength		λ		940		nm
Electrical Bandwidth	$V_r = 10 \text{ Volts}$	BWE		10		MHz
Reverse Light Current	$H = 5.0 \text{ mW/cm}^2, V_r = 5 \text{ V}$	IL	60	120		μA
Viewing Angle		$2 \theta_{1/2}$		140		Deg

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)